

isc N-Channel MOSFET Transistor

SPD04N80C3,ISPD04N80C3

• FEATURES

- Static drain-source on-resistance: $R_{DS}(on) \leq 1.3\Omega$
- Enhancement mode:
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

• High peak current capability

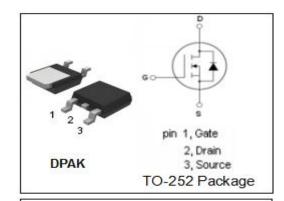
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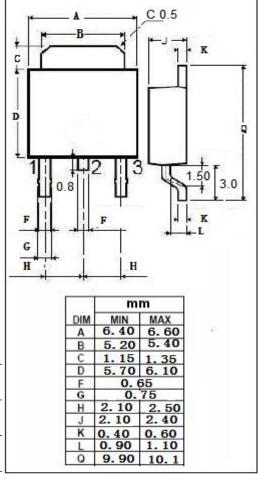
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
$V_{ extsf{DSS}}$	Drain-Source Voltage	800	V	
V _{GS}	Gate-Source Voltage	±20) V	
l _D	Drain Current-Continuous	4	А	
I _{DM}	Drain Current-Single Pulsed	12	А	
P_D	Total Dissipation @T _C =25℃	63	W	
Tj	Max. Operating Junction Temperature	150	$^{\circ}$	
T _{stg}	Storage Temperature -55~150		$^{\circ}$	

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT	
Rth(j-c)	j-c) Channel-to-case thermal resistance		°C/W	
Rth(j-a)	Channel-to-ambient thermal resistance	62	°C/W	







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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT			
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =0.25mA	800			V			
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D =0.24mA	2.1		3.9	V			
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =2.5A			1.3	Ω			
I _{GSS}	Gate-Source Leakage Current	V _{GS} =20V; V _{DS} =0V			0.1	μ A			
I _{DSS}	Drain-Source Leakage Current	V _{DS} =800V; V _{GS} = 0V			10	μ А			
V_{SD}	Diode forward voltage	I _F =4A, V _{GS} = 0V			1.2	V			

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